

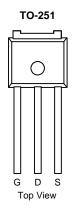
SW60N06V1-VB Datasheet N-Channel 60 V (D-S) MOSFET

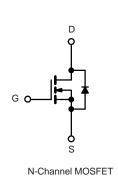
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a			
60	0.012at V _{GS} = 10 V	55			
	0.015 at V _{GS} = 4.5 V	47			

FEATURES

- 175 °C Junction Temperature
- Trench Power MOSFET
- Material categorization:







ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage	V_{GS}	± 20	V			
Continuous Drain Current (T _{.I} = 175 °C) ^b	T _C = 25 °C	I.	55			
Continuous Diain Current (1 _J = 175 °C) ²	T _C = 100 °C	- I _D	46 ^a			
Pulsed Drain Current	I _{DM}	110	Α			
Continuous Source Current (Diode Conduction)	I _S	50 ^a]			
Avalanche Current	I _{AS}	50]			
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	125	mJ		
Maximum Power Dissipation	T _C = 25 °C	P _D	136	W		
Maximum Fower Dissipation	T _A = 25 °C	' D	3 ^b , 8.3 ^{b, c}			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Mariana Landin to Ankinda	t ≤ 10 sec	D	15	18			
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	40	50	°C/W		
Maximum Junction-to-Case	·	R _{thJC}	0.85	1.1			

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. $t \le 10$ s.

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1



Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static			L				
Drain-Source Breakdown Voltage	V _{DS} V _{GS} = 0 V, I _D = 250 μA 60			V			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$			3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 60 V, V _{GS} = 0 V	1		1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250	1	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	60			Α	
		V _{GS} = 10 V, I _D = 20 A		0.012			
L	D	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.013			
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C		0.017		Ω	
		$V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$		0.015			
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		60		S	
Dynamic							
Input Capacitance	C _{iss}			3650			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		570		pF	
Reverse Transfer Capacitance	C _{rss}			325			
Total Gate Charge ^c	Qg			46			
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10		nC	
Gate-Drain Charge ^c	Q _{gd}			12			
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.6 Ω		15	25		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D\cong 50$ A, V_{GEN} = 10 V, R_g = 2.5 Ω		35	50	ns	
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)					
Pulsed Current	I _{SM}				60	Α	
Diode Forward Voltage	V_{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		45	100	ns	

Notes:

2

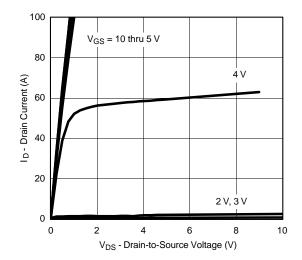
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

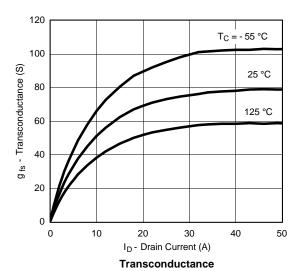
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TYPICAL CHARACTERISTICS (25 °C unless noted)



Output Characteristics



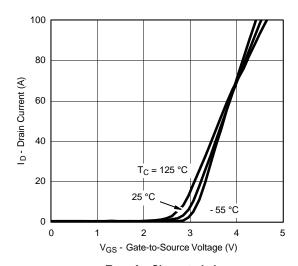
4200 3600 Ciss 3000 Ciss 2400 V 1800 U 1200 600

 V_{DS} - Drain-to-Source Voltage (V) $\label{eq:capacitance}$

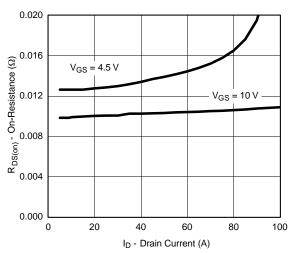
30

50

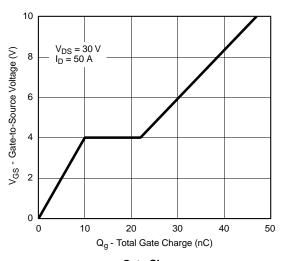
60



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

0 C_{rss}

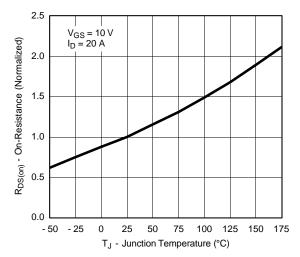
10

0

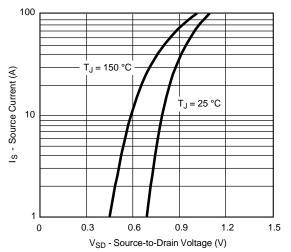
4800



TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature

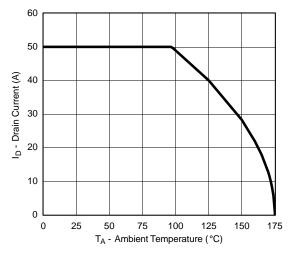


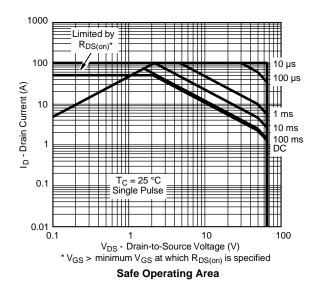
Source-Drain Diode Forward Voltage

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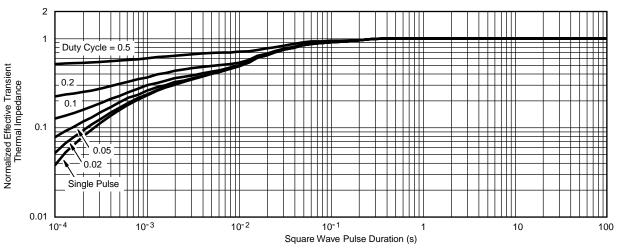


THERMAL RATINGS





Maximum Drain Current vs. Ambient Temperature



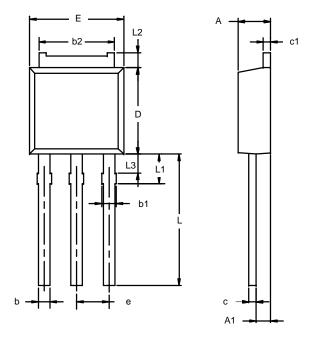
Normalized Thermal Transient Impedance, Junction-to-Case

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5



TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

	MILLIM	IETERS	INC	HES		
Dim	Min	Max	Min	Max		
Α	2.21	2.38	0.087	0.094		
A 1	0.89	1.14	0.035	0.045		
b	0.71	0.89	0.028	0.035		
b1	0.76	1.14	0.030	0.045		
b2	5.23	5.43	0.206	0.214		
С	0.46	0.58	0.018	0.023		
с1	0.46	0.58	0.018	0.023		
D	5.97	6.22	0.235	0.245		
E	6.48	6.73	0.255	0.265		
е	2.28	BSC	0.090 BSC			
L	8.89	9.53	0.350	0.375		
L1	1.91	2.28	0.075	0.090		
L2	0.89	1.27	0.035	0.050		
L3	1.15	1.52	0.045	0.060		
ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346						

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